

INFORMATION DISCLOSURE STATEMENT BY APPLICANT Sheet 1 of 1	COMPLETE IF KNOWN	
	Application Number	10/712,351
	Filing Date	November 13, 2003
	First Named Inventor	XU, et al.
	Art Unit	1775
	Examiner Name	Timothy M. Speer
	Attorney Docket Number	4241-685

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NON-PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITOL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
TS	AQ	D'EVELYN, M.P. et al., Growth and Characterization of Bulk GaN Crystals at High Pressure and High Temperature, Mat. Res. Soc. Symp. Proc. Vol. 798, pp. 275-279, 2004, Materials Research Society	

Examiner signature	/Timothy Speer/	Date Considered	02/07/2007
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*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

² Applicant is to place a check mark here if English Translation is attached. All the foreign patents and publications that are not written in English language are accompanied by their respective English abstracts, which constitute concise explanation of relevance of the non-English patents and publications that satisfy the requirements of 37 C.F.R. §1.98(a)(3)(i), according to MPEP 609 III A(3).